

ON Semiconductor

ISL9R1560G2-F085 15A, 600V Stealth Rectifier

Features

- High Speed Switching (t_{rr}=26ns(Typ.) @ I_F=15A)
- Low Forward Voltage(V_F=2.2V(Max.) @ I_F=15A)
- · Avalanche Energy Rated
- · AEC-Q101 Qualified

Applications

- · Automotive DCDC converter
- · Automotive On Board Charger
- · Switching Power Supply
- · Power Switching Circuits

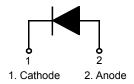
15A, 600V Stealth Rectifier

The ISL9R1560G2-F085 is StealthTM diode optimized for low loss performance in high frequency hard switched applications. The StealthTM family exhibits low reverse recovery current ($I_{RM(REC)}$) and exceptionally soft recovery under typical operating conditions.

This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I_{RRM} and short ta phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the Stealth diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Pin Assignments





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{RRM}	Peak Repetitive Reverse Voltage	600	V	
V _{RWM}	Working Peak Reverse Voltage	600	V	
V _R	DC Blocking Voltage	600	V	
I _{F(AV)}	Average Rectified Forward Current @ T _C = 25°C	15	Α	
I _{FSM}	Non-repetitive Peak Surge Current (Halfwave 1 Phase 50Hz)	45	Α	
E _{AVL}	Avalanche Energy (1A, 40mH)	20	mJ	
T _{J,} T _{STG}	Operating Junction and Storage Temperature	- 55 to +175	°C	

Thermal Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	0.93	°C/W
$R_{\theta,JA}$	Maximum Thermal Resistance, Junction to Ambient	45	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Tube	Quantity
ISL9R1560G2	ISL9R1560G2-F085	TO-247	-	30

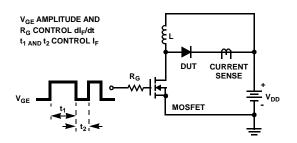
Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

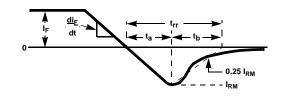
Symbol	Parameter	Conditions		Min.	Тур.	Max	Units
I _R	Instantaneous Reverse Current	V _R = 600V	T _C = 25 °C	-	-	100	uA
			T _C = 175 °C	-	-	2	mA
V _{FM} ¹	Instantaneous Forward Voltage	I _F = 15A	T _C = 25 °C T _C = 175 °C	-	1.8 1.35	2.2	V V
t _{rr} ²	Reverse Recovery Time	I _F =1A, di/dt = 200A/μs, V _{CC} = 390V	T _C = 25 °C	-	20	30	ns
		I_F =15A, di/dt = 200A/ μ s, V_{CC} = 390V	T _C = 25 °C T _C = 175 °C	-	26 114	40 -	ns ns
t _a t _b Q _{rr}	Reverse Recovery Time Reverse Recovery Charge	I_F =15A, di/dt = 200A/ μ s, V_{CC} = 390V	T _C = 25 °C	- - -	15 11 40	- - -	ns ns nC
E _{AVL}	Avalanche Energy	I _{AV} =1A,L = 40mH	•	20	-	-	mJ

Notes:

- 1. Pulse : Test Pulse width = $300\mu s$, Duty Cycle = 2%
- 2. Guaranteed by design

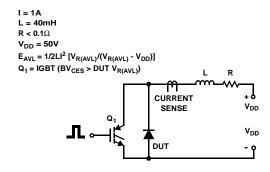
Test Circuit and Waveforms

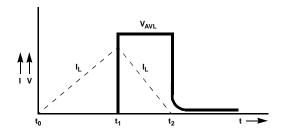




t_{rr} Test Circuit

t_{rr} Waveforms and Definitions





Avalanche Energy Test Circuit

Avalanche Current and Voltage Waveforms

Typical Performance Characteristics

Figure 1. Typical Forward Voltage Drop vs. Forward Current

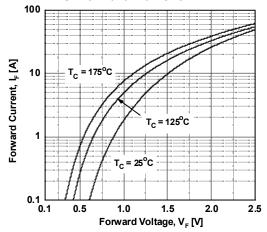


Figure 3. Typical Junction Capacitance

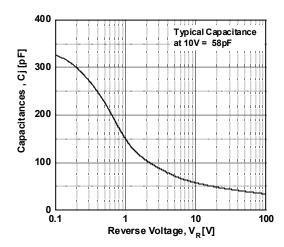


Figure 5. Typical Reverse Recovery Current vs. di/dt

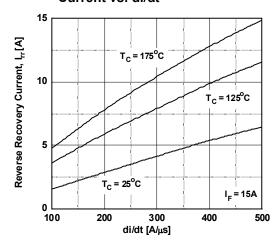


Figure 2. Typical Reverse Current vs.

Reverse Voltage

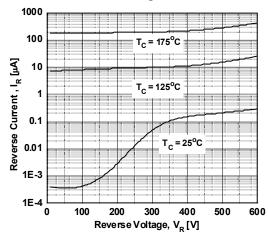


Figure 4. Typical Reverse Recovery Time vs. di/dt

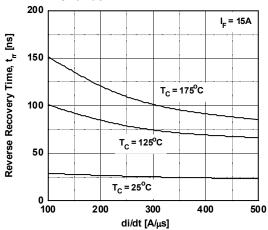
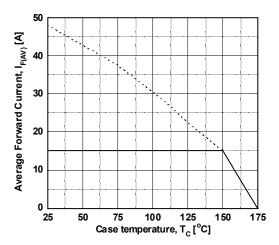


Figure 6. Forward Current Derating Curve



Typical Performance Characteristics (Continued)

Figure 7. Reverse Recovery Charge

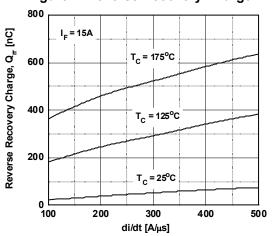
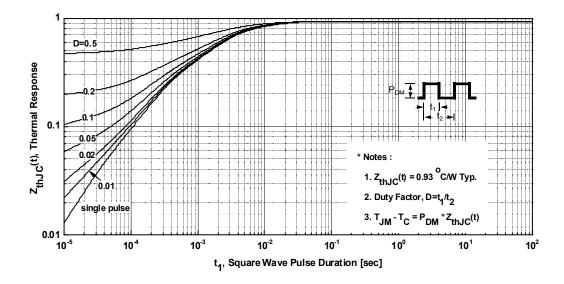
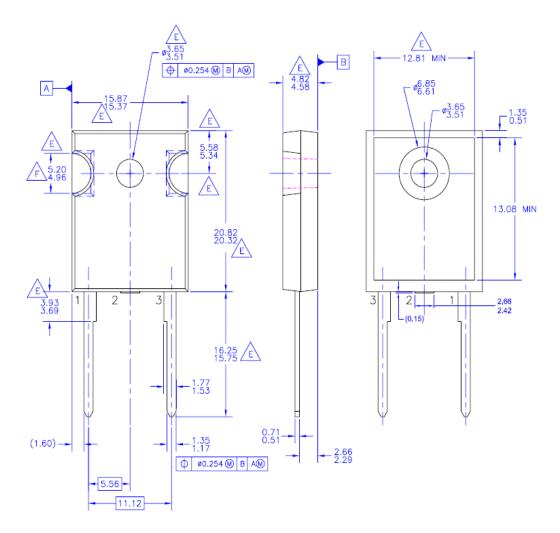


Figure 8. Transient Thermal Response Curve



Mechanical Dimensions

TO-247-2L



NOTES: UNLESS OTHERWISE SPECIFIED

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Dimensions in Millimeters

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